



High-end Power Semiconductor Manufacturer

ZK100A 2000-2600V

Fast Recovery Diode

- Low switching losses
- Low reverse recovery charge High
- power cycling capability



Average forward current	I _{FAV}	100 A		
Repetitive peak reverse voltage	V _{RRM}	2000–2600 V		
Reverse recovery time	t _{rr}	2.00, 2.50, 3.20, 4.00 μs		
V _{RRM} , V	2000	2200	2400	2600
Voltage code	20	22	24	26
T _j , °C		– 60 – 125		

MAXIMUM ALLOWABLE RATINGS

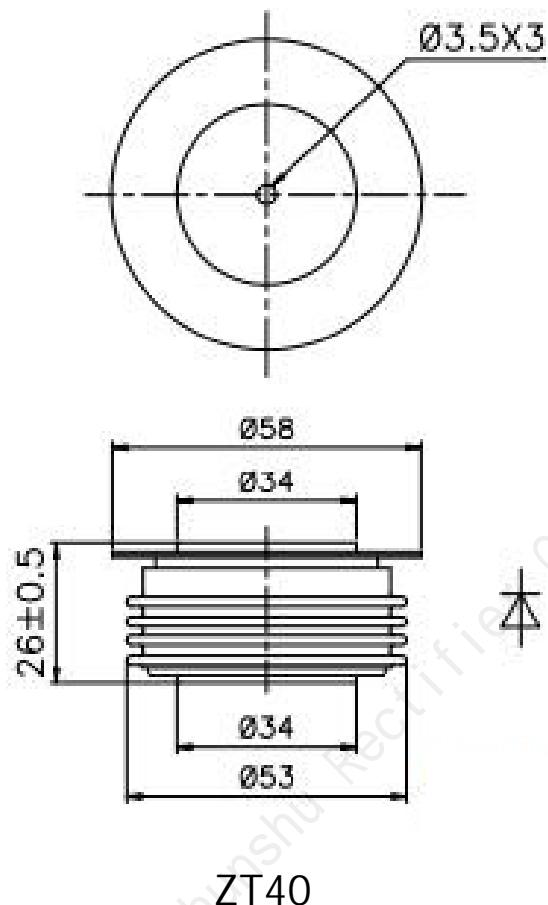
Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I _{FAV}	Average forward current	A	100	T _c =85 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I _{FRMS}	RMS forward current	A	157	T _c =85 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I _{FSM}	Surge forward current	kA	5.0	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V;
			5.8	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V;
I ² t	Safety factor	A ² s·10 ³	5.5	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V;
			6.5	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V;
BLOCKING					
V _{RRM}	Repetitive peak reverse voltages	V	2000–2600	T _{j min} < T _j <T _{j max} ; 180° half-sine wave; 50 Hz;	
V _{RSM}	Non-repetitive peak reverse voltages	V	2100–2700	T _{j min} < T _j <T _{j max} ; 180° half-sine wave; single pulse;	
V _R	Reverse continuous voltages	V	0.6·V _{RRM}	T _j =T _{j max} ;	
THERMAL					
T _{stg}	Storage temperature	°C	–60–55		
T _j	Operating junction temperature	°C	–60–125		
MECHANICAL					
F	Mounting force	kN	9.0–11.0		
a	Acceleration	m/s ²	50	Device clamped	

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V _{FM}	Peak forward voltage, max	V	3.50	T _j =25 °C; I _{FM} =314 A
V _{F(TO)}	Forward threshold voltage, max	V	1.35	T _j =T _{j max} ;
r _T	Forward slope resistance, max	mΩ	2.50	0.5 π I _{FAV} < I _T < 1.5 π I _{FAV}
BLOCKING				
I _{RRM}	Repetitive peak reverse current, max	mA	50	T _j =T _{j max} ; V _R =V _{RRM}
SWITCHING				
Q _{rr}	Total recovered charge, max	μC	60	
t _{rr}	Reverse recovery time ¹⁾ , max	μs	2.00, 2.50, 3.20, 4.00	T _j =T _{j max} ; I _{FM} = I _{FAV} ; di _R /dt=-100 A/μs;
I _{rrM}	Peak reverse recovery current, max	A	tbd*	V _R =100 V;
THERMAL				
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.0400	Double side cooled
R _{thjc-A}			0.0880	Direct current Anode side cooled
R _{thjc-K}			0.0720	Cathode side cooled
R _{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0080	Direct current
MECHANICAL				
W	Weight, max	g	180	
D _s	Surface creepage distance	mm (inch)	23.69 (0.933)	
D _a	Air strike distance	mm (inch)	19.10 (0.752)	

* **tbd** – data will be refined as additional tests are conducted and statistics are collected.

OVERALL DIMENSIONS



ZT40

All dimensions in millimeters